

Silicon PNP Power Transistors

BDX66C

DESCRIPTION

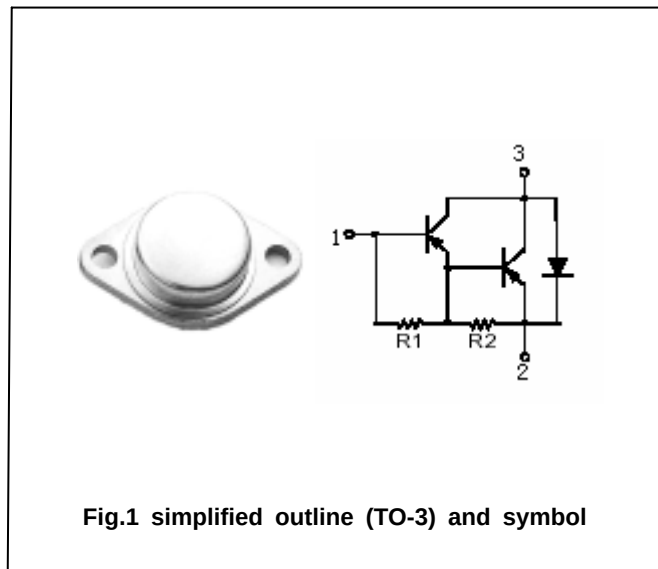
- With TO-3 package
- DARLINGTON
- High current

APPLICATIONS

- Designed for power amplification and switching applications.

PINNING (See Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-120	V
V_{CEO}	Collector-emitter voltage	Open base	-120	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-16	A
I_{CM}	Collector current(peak)		-20	A
I_B	Base current		-0.25	A
P_T	Total power dissipation	$T_C=25^\circ\text{C}$	150	W
T_j	Junction temperature		-55~200	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~200	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal resistance from junction to case	1.17	$^\circ\text{C/W}$

Silicon PNP Power Transistors

BDX66C

CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEQ(SUS)}	Collector-emitter sustaining voltage	I _C =-0.1A ; I _B =0; L=25mH	-120			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-10A ; I _B =-40mA			-2	V
I _{CBO}	Collector cut-off current	V _{CB} =-70V; I _E =0 T _C =150°C			-1 -5	mA
I _{CEO}	Collector cut-off current	V _{CE} =-60V; I _B =0			-3	mA
I _{EBO}	Emitter cut-off current	V _{EB} =-5V; I _C =0			-5	mA

Switching times

t _{on}	Turn-on time	I _C =-10A ; I _{B1} =-I _{B2} =0.04A V _{CC} =12V ;		1.0		μs
t _{off}	Turn-off time			3.5		μs

Silicon PNP Power Transistors

BDX66C

PACKAGE OUTLINE

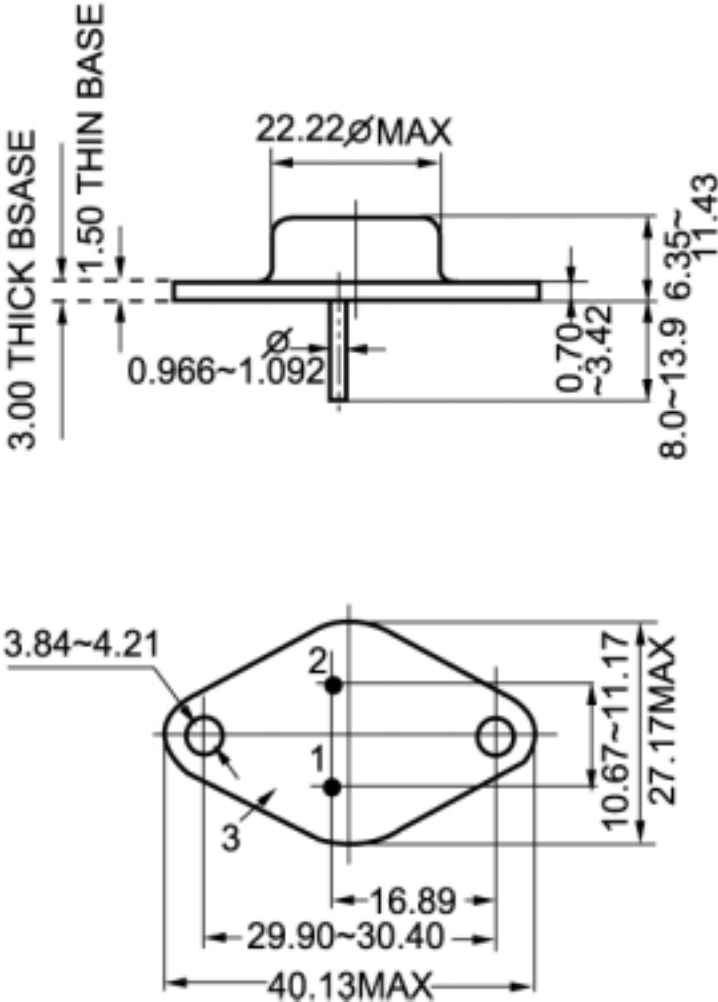


Fig.2 Outline dimensions